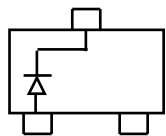
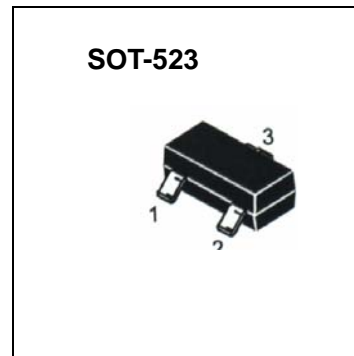


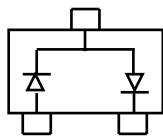
SCHOTTKY DIODE

FEATURES

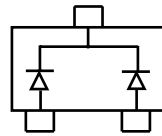
- Low Turn-on voltage
- Fast switching



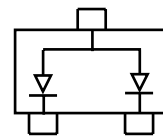
BAS70T Marking: 7C



BAS70-04T Marking: 7D



BAS70-05T Marking: 7E



BAS70-06T Marking: 7F

Maximum Ratings @T_A=25°C

Parameter	Symbol	Limits	Unit
Peak Repetitive Peak reverse voltage	V _{RRM}	70	V
Working Peak Reverse Voltage	V _{RWM}		
DC Blocking Voltage	V _R		
Forward Continuous Current	I _{FM}	70	mA
Non-Repetitive Peak Forward Surge Current @ t = 1.0s	I _{FSM}	100	A
Power Dissipation	P _D	150	mW
Thermal Resistance Junction to Ambient Air	R _{θJA}	833	°C/W
Storage temperature	T _{STG}	-65-125	°C

ELECTRICAL CHARACTERISTICS (T_{amb}=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Reverse breakdown voltage	V _{(BR)R}	I _R = 10μA	70		V
Reverse voltage leakage current	I _R	V _R =50V		100	nA
Forward voltage	V _F	I _F =1mA I _F =15mA		410 1000	mV
Diode capacitance	C _D	V _R =0, f=1MHz		2	pF
Reveres recovery time	t _{rr}	I _F =I _R =10mA, I _{rr} =0.1xI _R , R _L =100 Ω		5	nS

Typical Characteristics

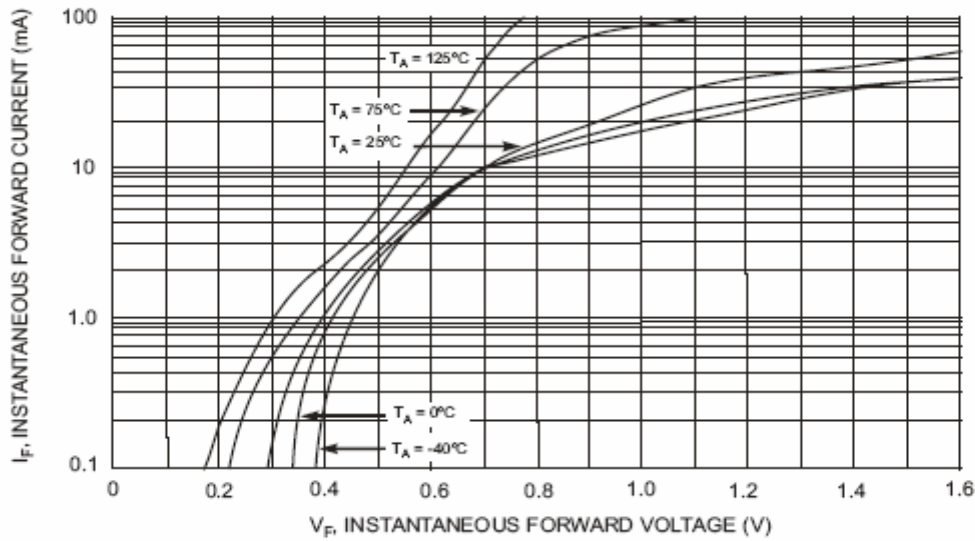


Fig. 1 Typical Forward Characteristics

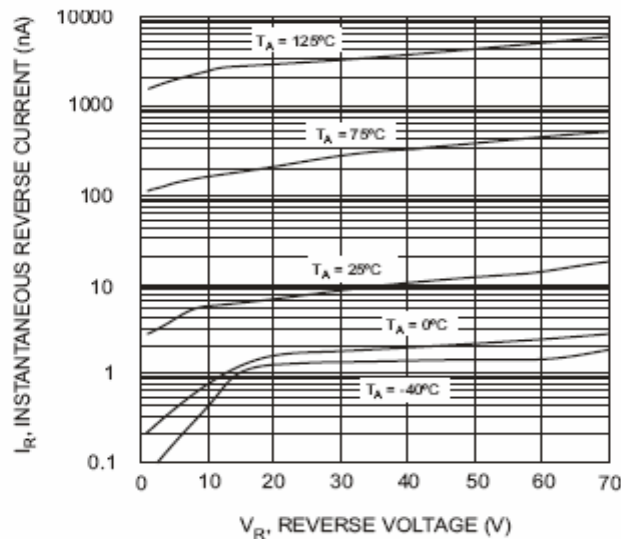


Fig. 2 Typical Reverse Characteristics

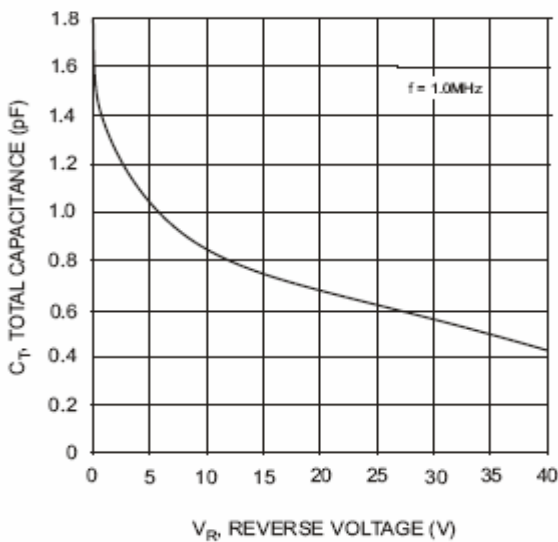


Fig. 3 Typical Capacitance

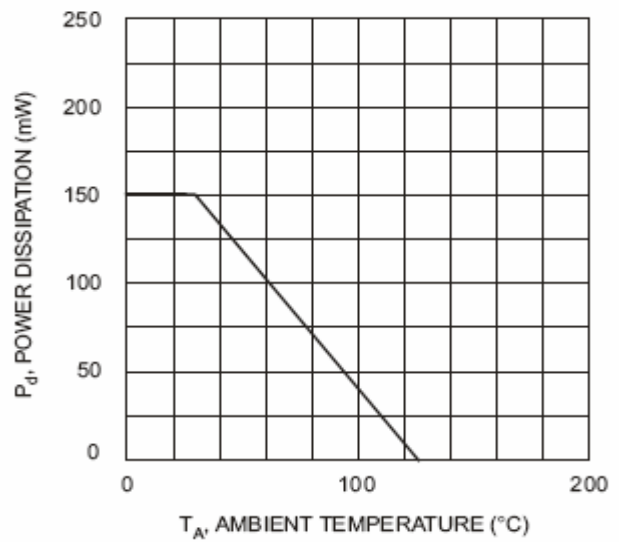


Fig. 4 Power Derating Curve, Total Package